TOSHIBA

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER MMIC AMPLIFIER TMD7185-2

FEATURES

- n HIGH POWER
 P1dB=33.0dBm at 7.1GHz to 8.5GHz
- n HIGH GAIN G1dB=28.0dB at 7.1GHz to 8.5GHz
- **n** BROAD BAND INTERNALLY MATCHED
- n HERMETICALLY SEALED PACKAGE

ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain Supply Voltage	VDD	V	15
Gate Supply Voltage	VGG	V	-10
Input Power	Pin	dBm	10. com
Flange Temperature	Tf	°C	-30 ~ +80
Storage Temperature	Tstg	°C	-65 ~ +175

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain	P1dB		dBm	32.0	33.0	CON
Compression Point		VDD= 10V		Total VI	.075	
Power Gain at 1dB Gain	G1dB	VGG= -5V	dB	27.0	28.0	
Compression Point	-47	13 (1) (1)				
Drain Current	IDD	f = 7.1 – 8.5GHz	Α		1.4	1.7
Input VSWR	VSWRin					3.0
3 rd Order Intermodulation	IM_3	Po (S.C.L.)=22.0 dBm	dBc	-42	-45	_
Distortion					-51	4100
					DZSC	

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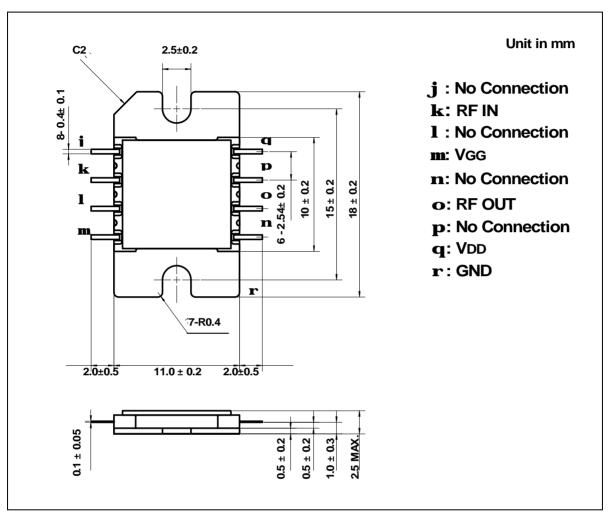
The information contained herein is subject to change without prior notice. It is therefor advisable to contact TOSHIBA before proceeding with design of equipment incorporating this product.



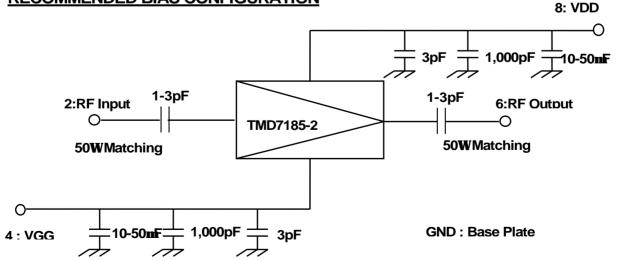
TOSHIBA CORPORATION

Rev. Mar.2006

PACKAGE OUTLINE (2-11E1B)



RECOMMENDED BIAS CONFIGURATION



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C. Flanges of devices should be attached using screws and washers. Recommended torque is 0.18-0.20 N·m.